

Silicon PNP Power Transistors

BD244/A/B/C

DESCRIPTION

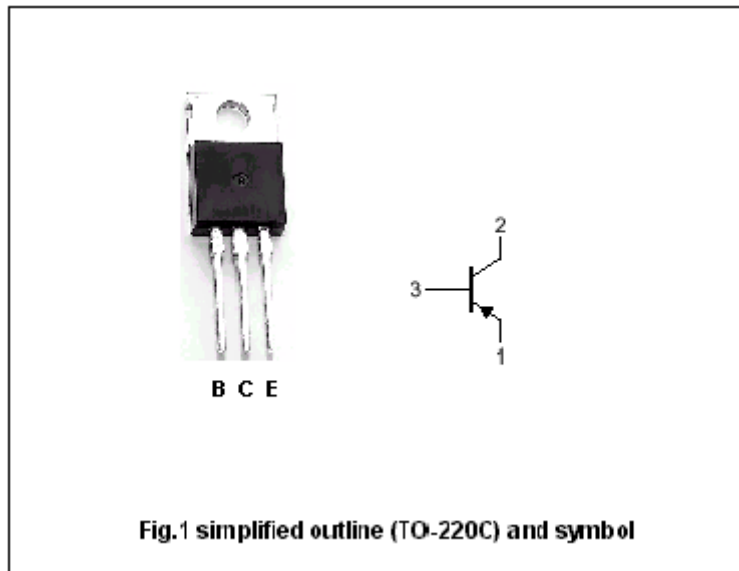
- With TO-220C package
- Complement to type BD243/A/B/C

APPLICATIONS

- For medium power linear and switching applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	BD244	Open emitter	-45	V
		BD244A		-60	
		BD244B		-80	
		BD244C		-100	
V_{CEO}	Collector-emitter voltage	BD244	Open base	-45	V
		BD244A		-60	
		BD244B		-80	
		BD244C		-100	
V_{EBO}	Emitter-base voltage		Open collector	-5	V
I_C	Collector current			-6	A
I_{CM}	Collector current-peak			-10	A
I_B	Base current			-2	A
P_C	Collector power dissipation		$T_C=25^\circ\text{C}$	65	W
T_j	Junction temperature			150	$^\circ\text{C}$
T_{stg}	Storage temperature			-65~150	$^\circ\text{C}$

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE0(SUS)}	Collector-emitter sustaining voltage	BD244	I _C =-30mA; I _B =0	-45			V
		BD244A		-60			
		BD244B		-80			
		BD244C		-100			
V _{CEsat}	Collector-emitter saturation voltage		I _C =-6A; I _B =-1 A			-1.5	V
V _{BE}	Base-emitter on voltage		I _C =-6A ; V _{CE} =-4V			-2.0	V
I _{CEO}	Collector cut-off current	BD244/A	V _{CE} =-30V; I _B =0			-0.7	mA
		BD244B/C	V _{CE} =-60V; I _B =0				
I _{CES}	Collector cut-off current	BD244	V _{CE} =-45V; V _{BE} =0			-0.4	mA
		BD244A	V _{CE} =-60V; V _{BE} =0				
		BD244B	V _{CE} =-80V; V _{BE} =0				
		BD244C	V _{CE} =-100V; V _{BE} =0				
I _{EBO}	Emitter cut-off current		V _{EB} =-5V; I _C =0			1	mA
h _{FE-1}	DC current gain		I _C =-0.3A ; V _{CE} =-4V	30			
h _{FE-2}	DC current gain		I _C =-3A ; V _{CE} =-4V	15			

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PACKAGE OUTLINE

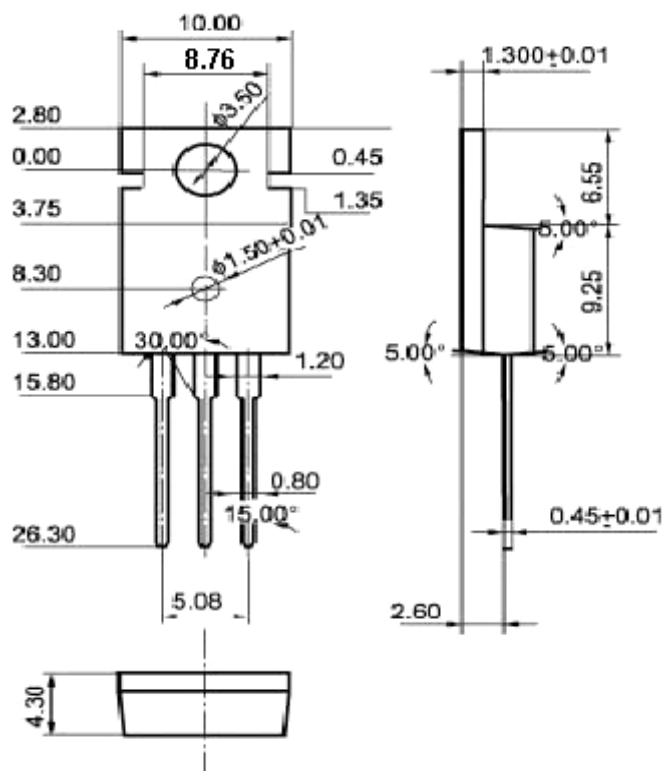


Fig.2 Outline dimensions (unindicated tolerance: ± 0.10 mm)